

BAS216WT-AH

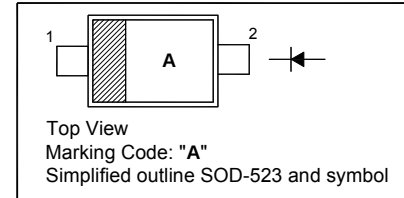
Silicon Epitaxial Planar Switching Diode

Features

- AEC-Q101 Qualified and PPAP Capable
- Halogen and Antimony Free(HAF), RoHS compliant

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

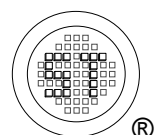


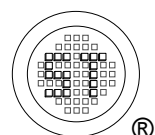
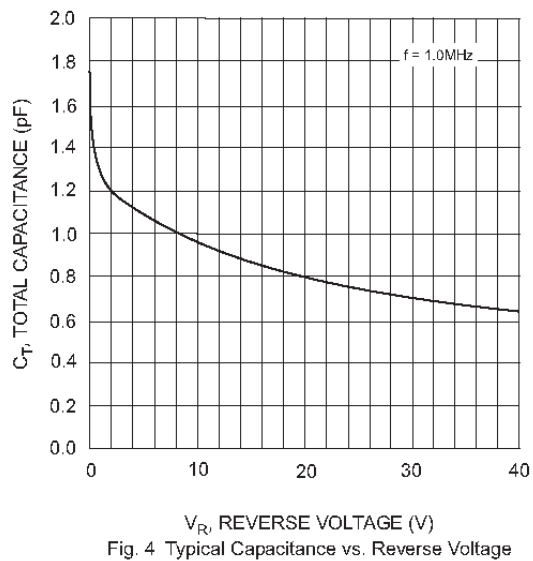
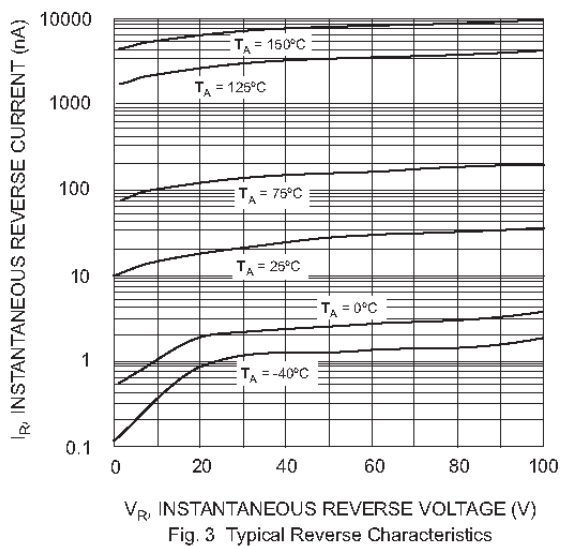
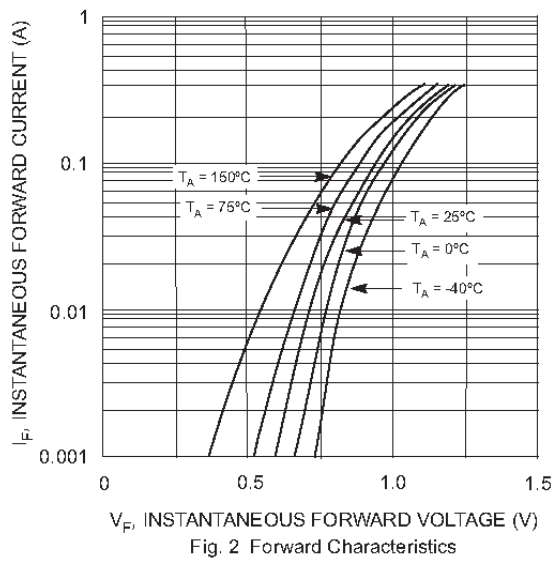
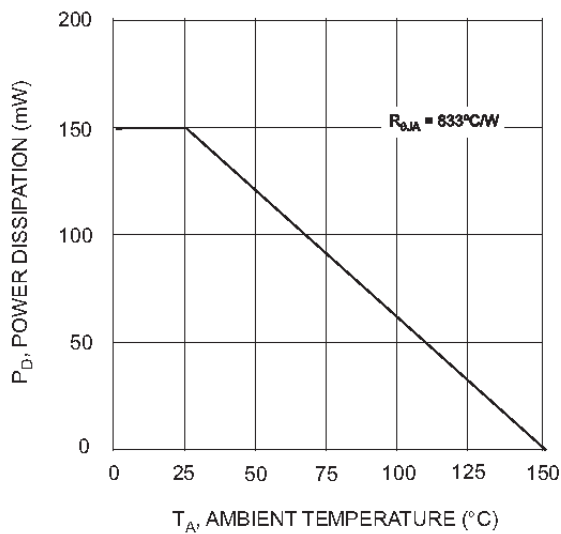
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	85	V
Reverse Voltage	V_R	75	V
Continuous Forward Current	I_F	250	mA
Repetitive Peak Forward Current	I_{FRM}	500	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	4	A
at $t = 1\ \mu\text{s}$		1	
at $t = 1\ \text{ms}$		0.5	
at $t = 1\ \text{s}$			
Power Dissipation	P_{tot}	150	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1\ \text{mA}$ at $I_F = 10\ \text{mA}$ at $I_F = 50\ \text{mA}$ at $I_F = 150\ \text{mA}$	V_F	715 855 1000 1250	mV
Reverse Current at $V_R = 25\ \text{V}$ at $V_R = 75\ \text{V}$ at $V_R = 25\ \text{V}$, $T_J = 150^\circ\text{C}$ at $V_R = 75\ \text{V}$, $T_J = 150^\circ\text{C}$	I_R	30 1 30 50	nA μA μA μA
Diode Capacitance at $V_R = 0\ \text{V}$, $f = 1\ \text{MHz}$	C_{tot}	1.5	pF
Reverse Recovery Time at $I_F = 10\ \text{mA}$ to $I_R = 10\ \text{mA}$, $I_R = 1\ \text{mA}$, $R_L = 100\ \Omega$	t_{rr}	4	ns



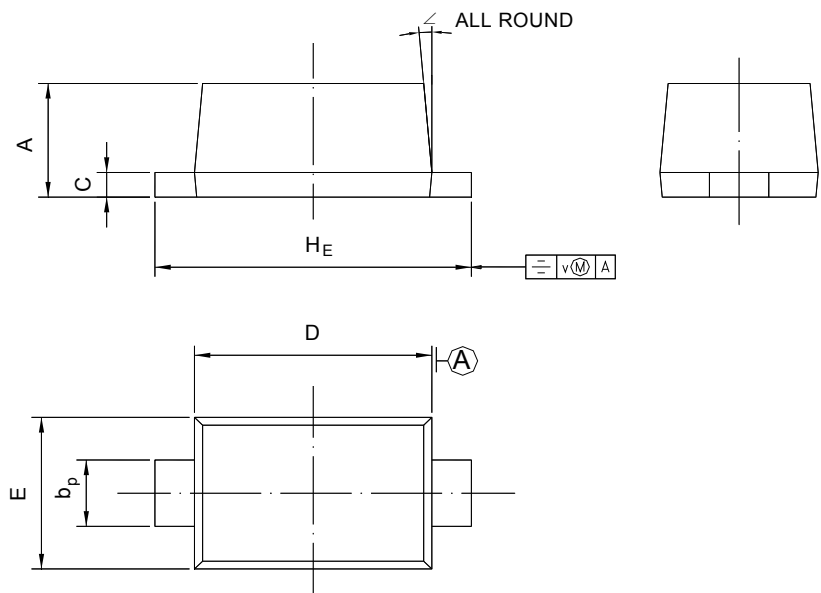


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PACKAGE OUTLINE

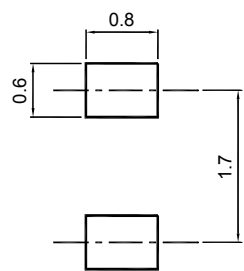
Plastic surface mounted package; 2 leads

SOD-523



UNIT	A	b _p	C	D	E	H _E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°

Recommended Soldering Footprint



SOD-523

Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	(inch)	mm	(inch)	
SOD-523	8	4 ± 0.1	0.157 ± 0.004	178	7	4,000

